Power Transistor, PNP, General Purpose
100 V, 3 A

MJK32C

These Bipolar Junction Transistors are designed for general purpose power and switching applications such as regulators, converters and power amplifiers. Housed in advanced LFPAK package (5 x 6 mm) with excellent thermal conduction. Automotive end applications include air bag deployment, power train control units, and instrument clusters.

Features

- Complementary NPN: MJK31C
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_A = 25°C)

Rating	Symbol	Max	Unit
Collector−Emitter Voltage	V_{CEO}	−100	Vdc
Emitter−Base Voltage	V_{EBO}	−5	Vdc
Collector Current − Continuous	I_C	−3	A
Collector Current − Peak	I_{CM}	−5	A
Junction and Storage Temperature Range	T_J, T_{stg}	−65 to +150	°C

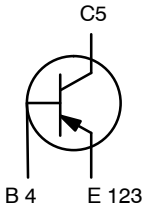
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction−to−Case per Device (Note 1)	$R_{\theta JC}$	2.4	°C/W
Thermal Resistance, Junction−to−Ambient per Device (Note 1)	$R_{\theta JA}$	45	°C/W
Total Power Dissipation @ T_A = 25°C (Note 1)	P_D	2.7	W

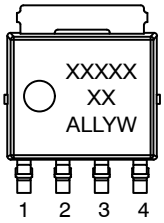
1. Surface−mounted on FR4 board using a 6 cm^2, 2 oz. Cu collector pad.

PNP TRANSISTOR
100 V, 3 A



LFPAK4 5x6
CASE 760AB

MARKING DIAGRAM



(Top View)

XXXXXX	= Specific Device Code
A	= Assembly Location
LL	= Wafer Lot
Y	= Year
W	= Work Week

ORDERING INFORMATION

Device	Package	Shipping†
MJK32CTWG	LFPAK4 5x6 (Pb−Free)	3000 / Tape & Reel
NJVMJK32CTWG	LFPAK4 5x6 (Pb−Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector−Emitter Sustaining Voltage (I_C = −30 mA, I_B = 0)	$V_{CEO(sus)}$	−100	–	–	Vdc
Collector Cutoff Current (V_{CE} = Rated V_{CEO}, V_{BE} = 0)	I_{CES}	–	–	−20	μA
Collector Cutoff Current (V_{CE} = Rated V_{CEO}, I_B = 0)	I_{CEO}	–	–	−50	μA
Emitter Cutoff Current (V_{EB} = −5 Vdc)	I_{EBO}	–	–	−1.0	mA
ON CHARACTERISTICS					
Collector−Emitter Saturation Voltage (I_C = −3 Adc, I_B = −0.375 Adc)	$V_{CE(sat)}$	–	–	−1.2	Vdc
Base−Emitter Saturation Voltage (I_C = −3 Adc, V_{CE} = −4 Vdc)	$V_{BE(on)}$	–	–	−1.8	Vdc
DC Current Gain (V_{CE} = −4 Vdc, I_C = −1 Adc) (V_{CE} = −4 Vdc, I_C = −3 Adc)	h_{FE}	25 10	– –	– 60	–
DYNAMIC CHARACTERISTICS					
Gain Bandwidth Product (I_C = 0.5 Adc, V_{CE} = 10 Vdc, f = 1 MHz)	f_T	–	3	–	MHz

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

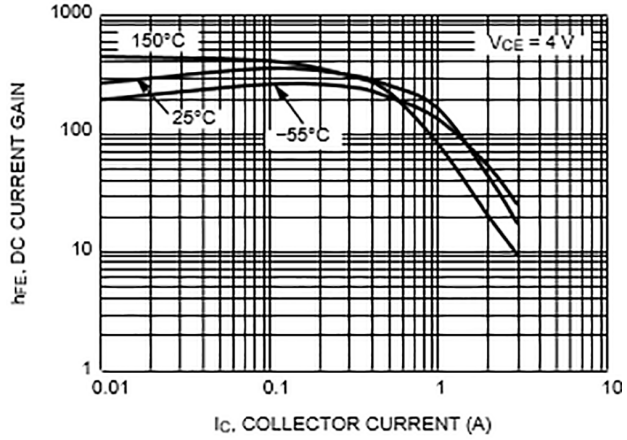


Figure 1. DC Current Gain

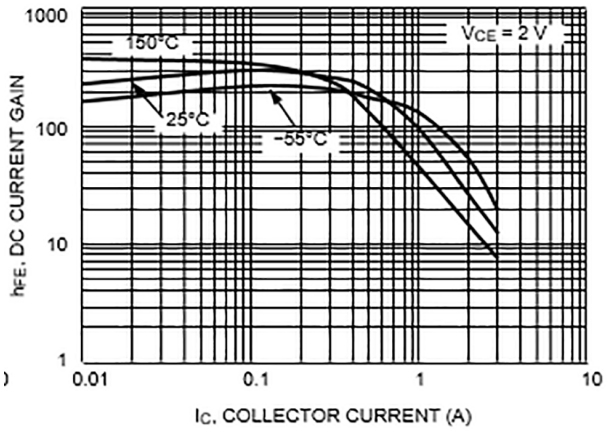


Figure 2. DC Current Gain

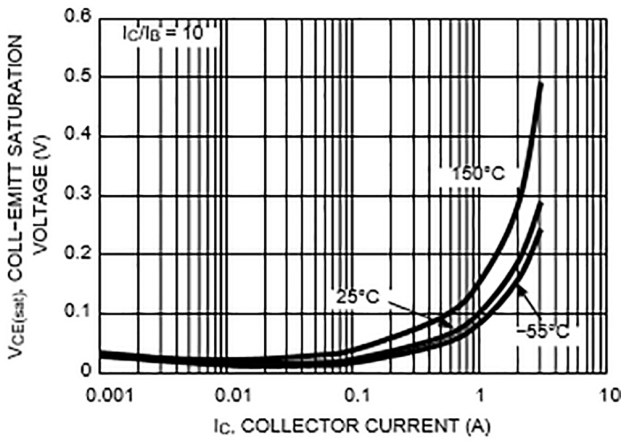


Figure 3. Saturation Voltage $V_{CE(sat)}$

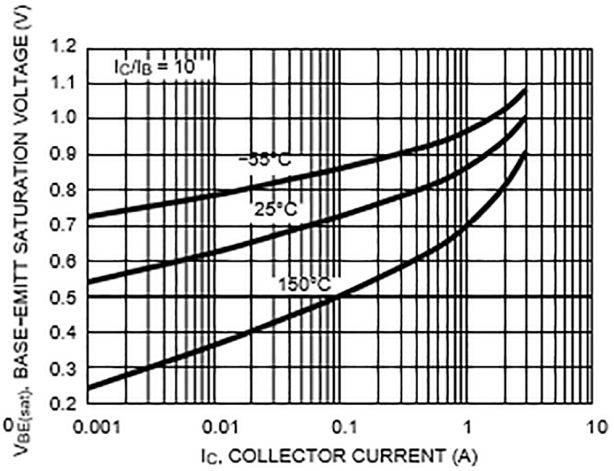


Figure 4. Saturation Voltage $V_{BE(sat)}$

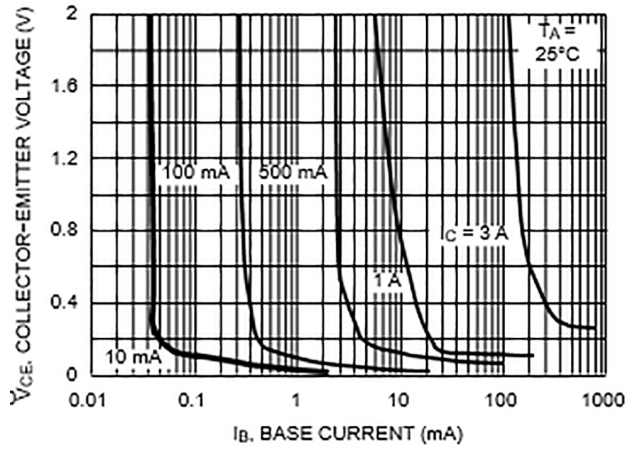


Figure 5. Collector Saturation Region

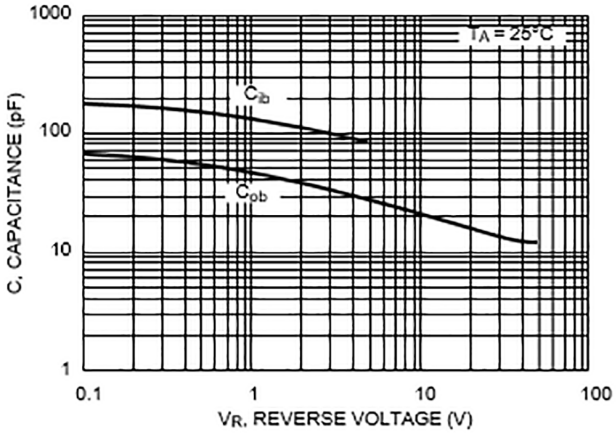


Figure 6. Capacitance

TYPICAL CHARACTERISTICS (continued)

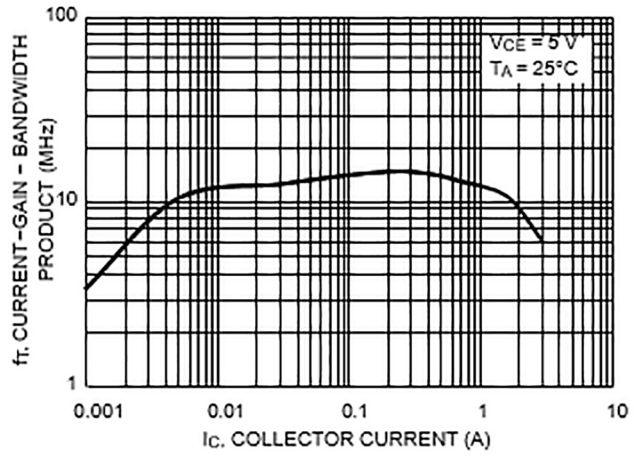


Figure 7. Current−Gain−Bandwidth Product

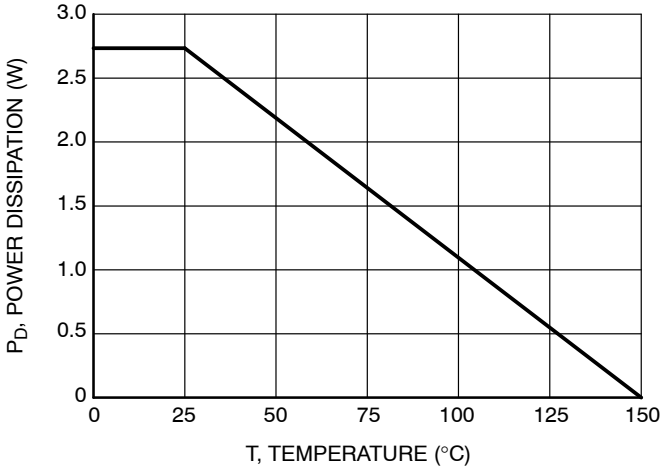


Figure 8. Power Derating

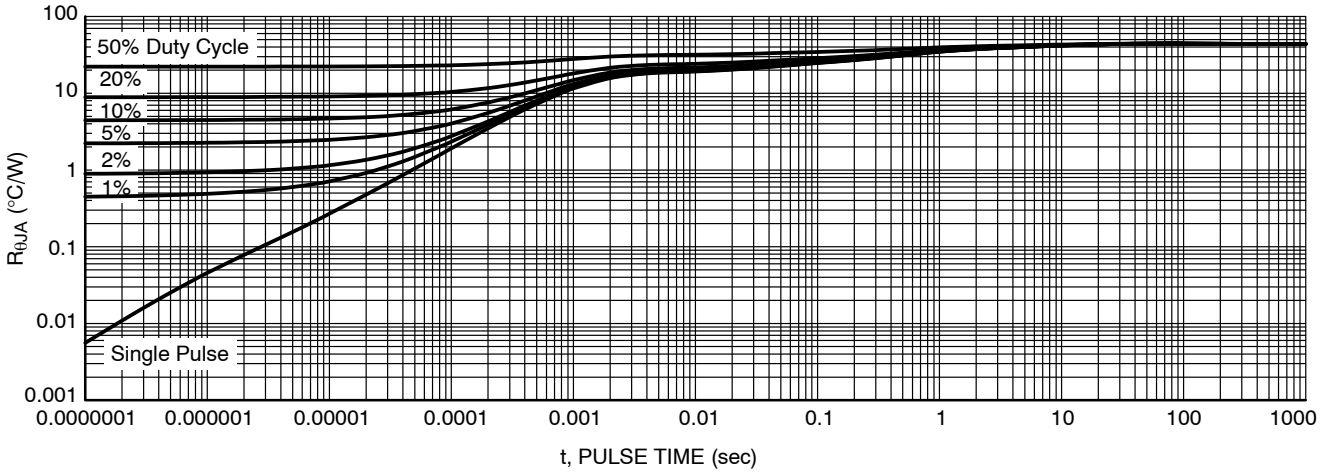
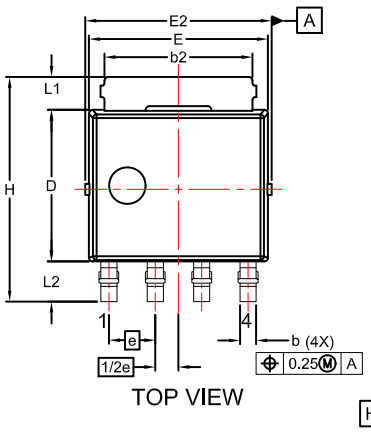


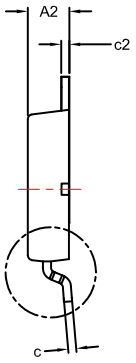
Figure 9. Typical Transient Thermal Response, Junction−to−Case

PACKAGE DIMENSIONS

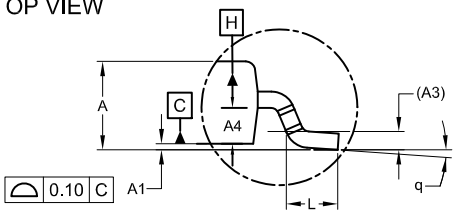
LFPAK4 5x6
CASE 760AB
ISSUE C

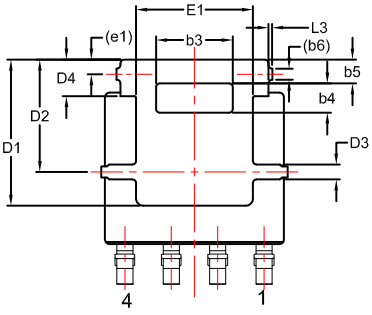


TOP VIEW



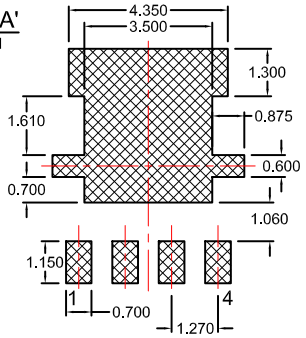
SIDE VIEW





BOTTOM VIEW

DETAIL 'A'
SCALE: 2:1



RECOMMENDED LAND PATTERN

*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.150mm PER SIDE.
4. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

UNIT IN MILLIMETER			
DIM	MIN	NOM	MAX
A	1.10	1.20	1.30
A1	0.00	0.08	0.15
A2	1.10	1.15	1.20
A3	0.25 REF		
A4	0.45	0.50	0.55
b	0.40	0.45	0.50
b2	3.80	4.10	4.40
b3	2.00	2.10	2.20
b4	0.70	0.80	0.90
b5	0.55	0.65	0.75
b6	0.31 REF		
c	0.19	0.22	0.25
c2	0.19	0.22	0.25
D	4.05	4.15	4.25
D1	3.80	4.00	4.20
D2	3.00	3.10	3.20
D3	0.30	0.40	0.50
D4	0.90	1.00	1.10
E	4.80	4.90	5.00
E1	3.10	3.20	3.30
E2	5.00	5.15	5.30
e	1.27 BSC		
1/2e	0.635 BSC		
e1	0.40 REF		
H	6.00	6.15	6.30
L	0.40	0.65	0.85
L1	0.80	0.90	1.00
L2	0.90	1.10	1.30
L3	0.00	0.10	0.20
q	0°	4°	8°

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
Technical Library: www.onsemi.com/design/resources/technical−documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support
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